IRF3707SPBF-VB Datasheet

N-Channel 30 V (D-S) 175 °C MOSFET

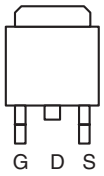
PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.006
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.008
I_D (A)	70
Configuration	Single
Package	TO-220AB/ TO-263

FEATURES

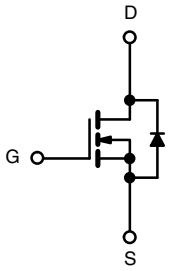
- Trench power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested

RoHS COMPLIANT
HALOGEN FREE

TO-263



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C [a]	I_D	70	A
	T_C = 125 °C		50	
Continuous Source Current (Diode Conduction) [a]		I_S	70	
Pulsed Drain Current [b]		I_{DM}	250	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	33	
Single Pulse Avalanche Energy		E_{AS}	54	mJ
Maximum Power Dissipation [b]	T_C = 25 °C	P_D	71	W
	T_C = 125 °C		23	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Junction-to-Ambient	PCB Mount [c]	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	2.1	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR4 material).

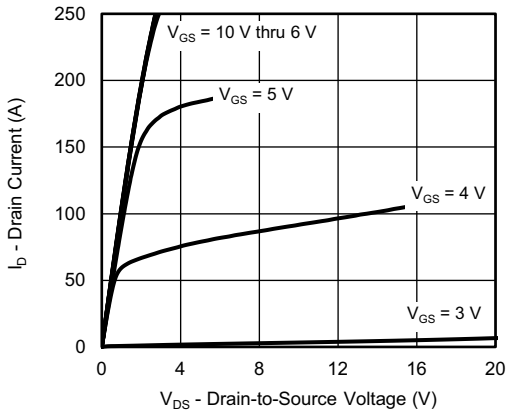
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		30	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		1.5	2.0	2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 30 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 30 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 30 V, T_J = 175 °C	-	-	150	
On-State Drain Current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	70	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 20 A	-	0.006	-	Ω
		V_{GS} = 10 V	I_D = 20 A, T_J = 125 °C	-	0.0094	-	
		V_{GS} = 10 V	I_D = 20 A, T_J = 175 °C	-	0.0115	-	
		V_{GS} = 4.5 V	I_D = 15 A	-	0.008	-	
Forward Transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 15 A		-	100	-	S
Dynamic [b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	1850	2200	pF
Output Capacitance	C_{oss}			-	260	400	
Reverse Transfer Capacitance	C_{rss}			-	95	200	
Total Gate Charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 50 A	-	46	75	nC
Gate-Source Charge [c]	Q_{gs}			-	10	-	
Gate-Drain Charge [c]	Q_{gd}			-	8	-	
Gate Resistance	R_g	f = 1 MHz		1.3	2.8	4.5	Ω
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 0.4 Ω I_D ≅ 50 A, V_{GEN} = 10 V, R_g = 1 Ω		-	9	15	ns
Rise Time [c]	t_r			-	19	30	
Turn-Off Delay Time [c]	$t_{d(off)}$			-	26	40	
Fall Time [c]	t_f			-	10	15	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed Current [a]	I_{SM}			-	-	200	A
Forward Voltage	V_{SD}	I_F = 30 A, V_{GS} = 0 V		-	0.87	1.5	V

Notes

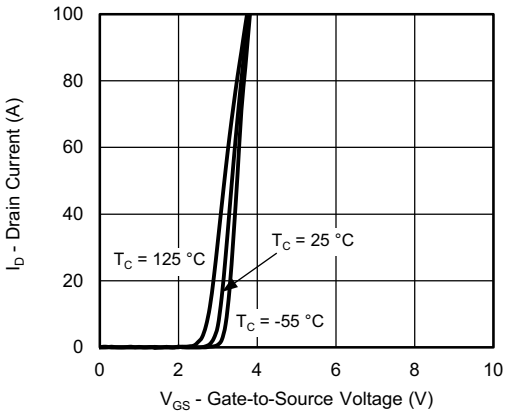
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

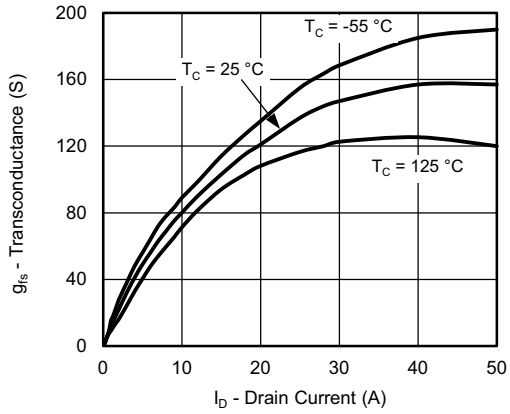
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



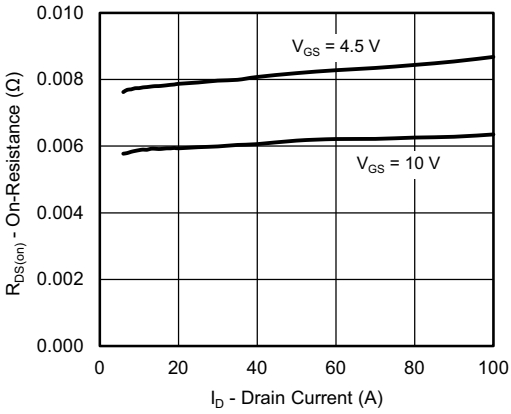
Output Characteristics



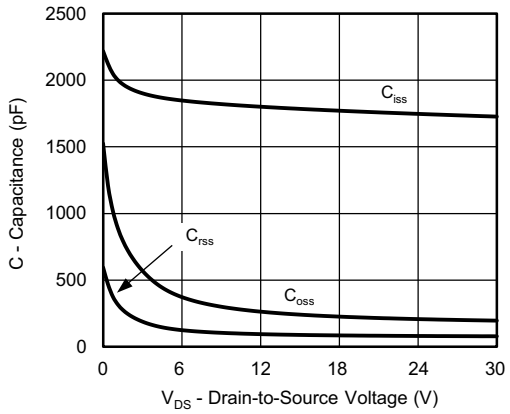
Transfer Characteristics



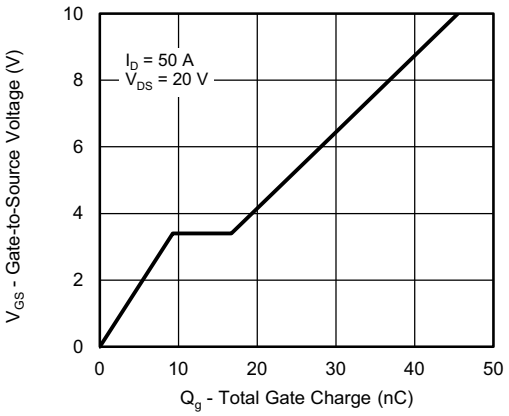
Transconductance



On-Resistance vs. Drain Current

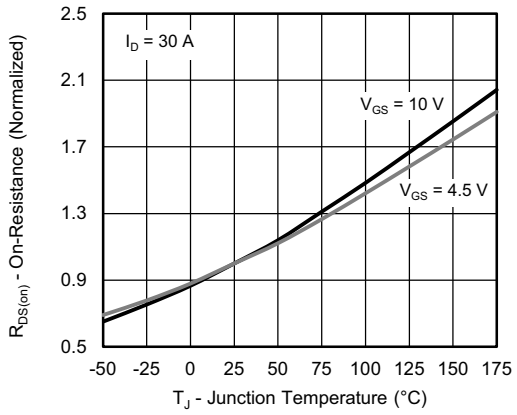


Capacitance

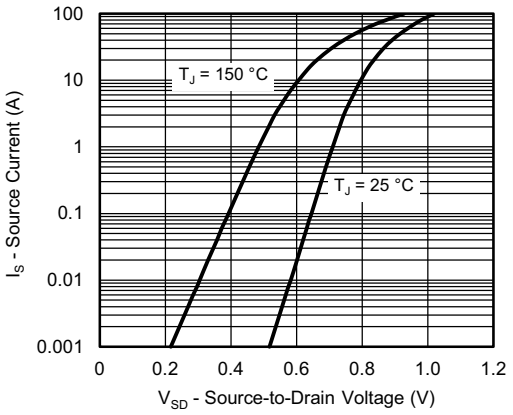


Gate Charge

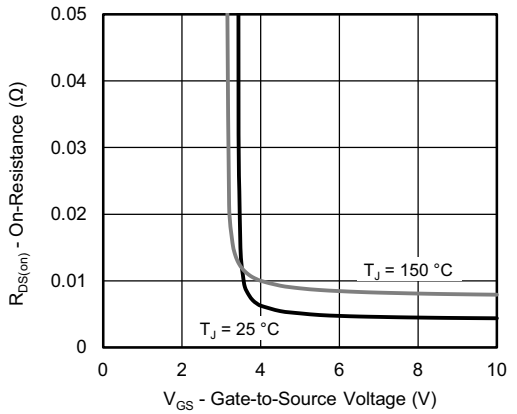
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



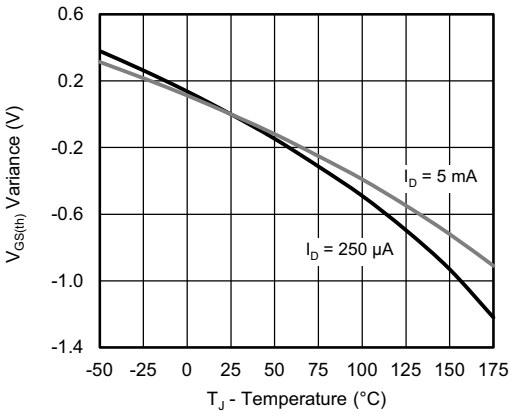
On-Resistance vs. Junction Temperature



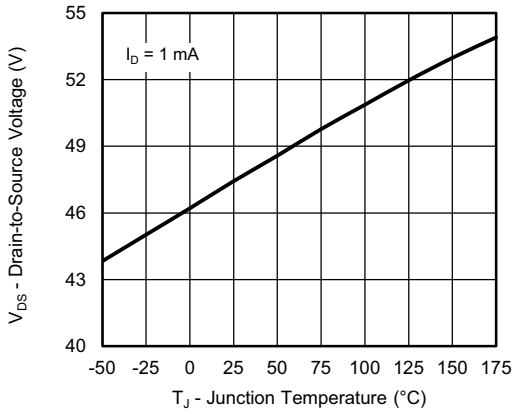
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

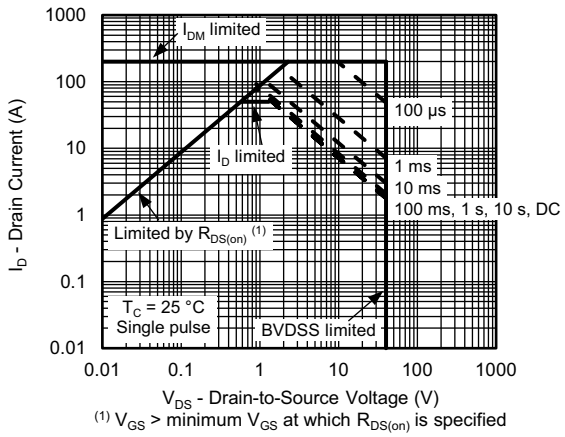


Threshold Voltage

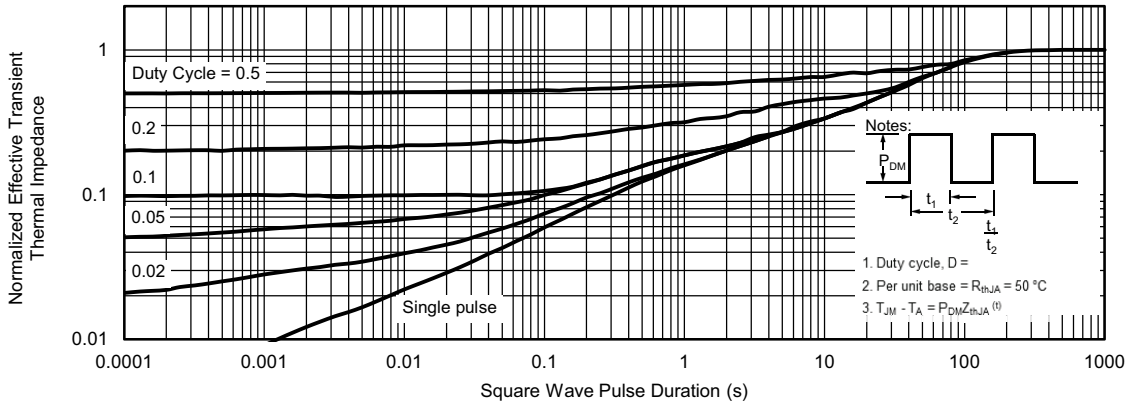


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

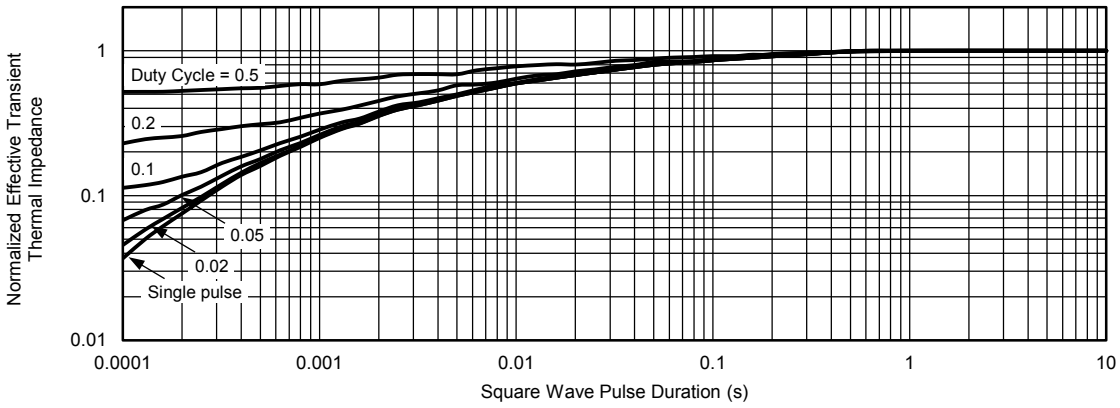


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



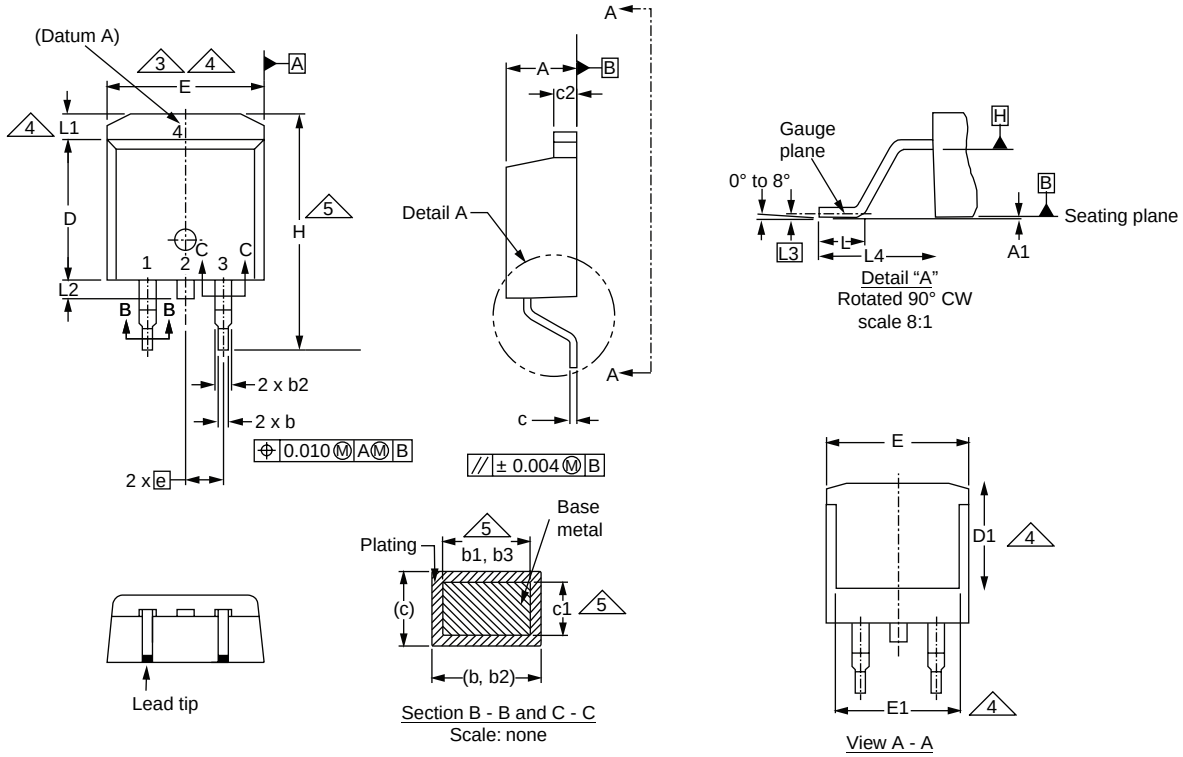
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-263AB



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

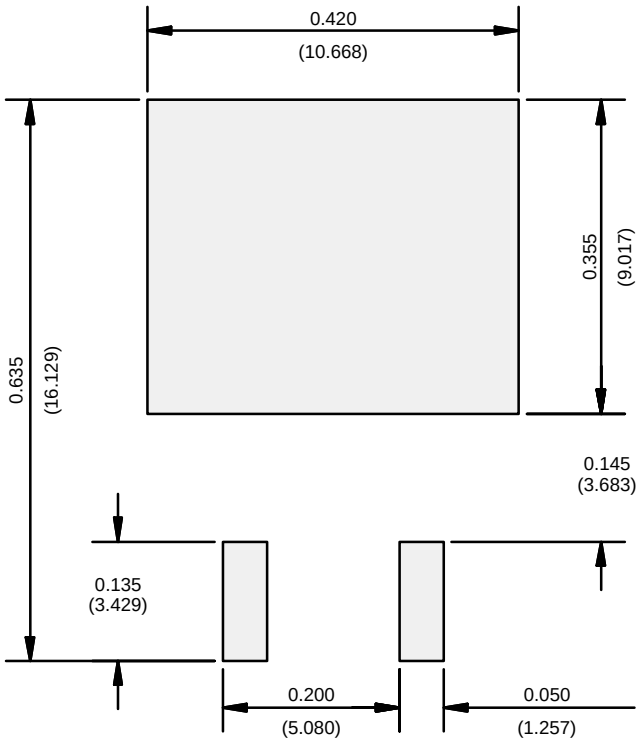
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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